

CG51/CE51 SERIES

3V, 0.50 MICRON HIGH PERFORMANCE/LOW POWER CMOS GATE ARRAYS

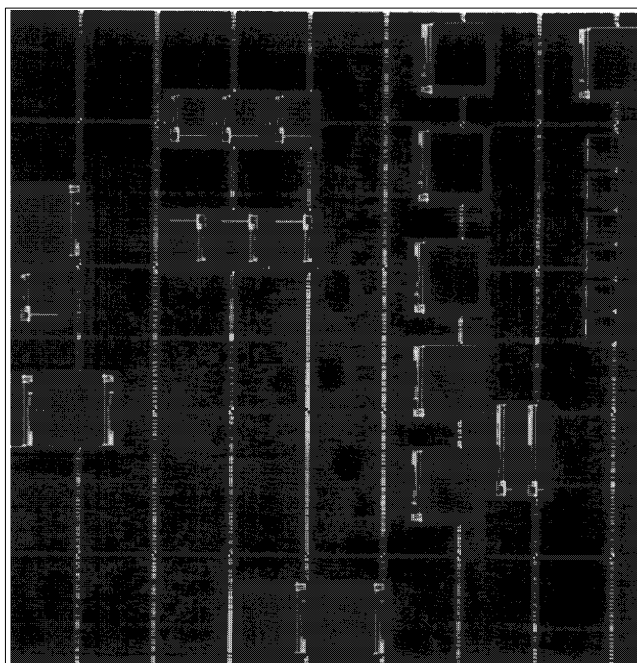
DESCRIPTION

The Fujitsu CG51/CE51 is a series of ultra high performance CMOS gate arrays. The CG51 is a high density Sea-of-Gates array for applications requiring high levels of integration or low power. The CE51 is a high performance embedded gate array family offering full support of diffused high speed RAMS, ROMS and embedded megafunctions. The CE51 series offers density and performance approaching that achievable with standard cell solutions with the time-to-market advantage of a gate array.

True 3V products, the CG51/CE51 feature very low power (1.2 microwatt/Mhz) and both 3.3V and 5.0V compatible I/Os. These advanced product families are targeted at users who are seeking very high performance or very high levels of integration. Potential end-user applications include computers, supercomputers, workstations, graphic terminals, telecom networking, and signal processing.

FEATURES

- 0.5 Micron Drawn Channel Length
- Triple layer metal
- 3.3V \pm 0.3V supply voltage
- Chanelless, Sea-of-gates Architecture
- Internal gate delay of 210ps, F/O = 2, L = 1mm
- Low power consumption: 1.2 microwatt/gate/Mhz
- Maximum toggle frequency: 600Mhz
- High speed I/Os: PCML (PECL), LVTC
- Supports 3.3V and 5.0V I/O
- RAM compiler supports Single/Dual/Triple port RAM
- Supports JTAG boundary scan, full and partial scan
- Phase Locked Loop for interchip clock skew control
- Clock net for optimized on-chip clock skew control
- Advanced packaging options include QFP, PGA, BGA, and MCM
- High drive capability: 2, 4, 8, 12, or 24mA
- Supports all major third party EDA tools including: Cadence, Mentor, Synopsys



Fujitsu Microelectronics, Inc.'s CE51654
647,000 Available Gate .5 Micron Embedded
Array, Containing 28 Embedded Macro Cells

PRODUCT SUMMARY

Device Name	Available Gates	Number of Pads	Metal Wiring
CG51754	753,768	496	3LM
CG51654	647,948	456	3LM
CG51484	477,632	400	3LM
CG51364	363,084	352	3LM
CG51284	277,380	304	3LM
CG51214	214,760	272	3LM
CG51164	160,140	240	3LM
CG51114	113,520	208	3LM
CG51343	34,272	120	3LM

CG51/CE51 SERIES

DC CHARACTERISTICS

Measuring conditions: $V_{DD} = 3.3V \pm 0.3V$, $V_{SS} = 0V$, $T_j = -0$ to $100^{\circ}C$

Parameter	Symbol	Test Conditions		Requirements			Unit
				Min.	Typ.	Max.	
Supply current ²	I_{DDs}	Standby mode ¹	CG51343 to CG51214	-1.0	-	1.0	mA
			CG51284 to CG51484	-2.0	-	2.0	
			CG51654 to CG51754	-3.0	-	3.0	
High-level input voltage ³	V_{IH}	CMOS level	Normal cell	$V_{DD} \times 0.7$	-	V_{DD}	V
			Schmitt trigger cell	$V_{DD} \times 0.8$	-	V_{DD}	
		TTL level	Normal cell	2.2	-	V_{DD}	
Low-level input voltage ³	V_{IL}	CMOS level	Normal cell	V_{SS}	-	$V_{DD} \times 0.2$	V
			Schmitt trigger cell	V_{SS}	-	$V_{DD} \times 0.2$	
		TTL level	Normal cell	V_{SS}	-	0.8	
High-level output voltage	V_{OH}	$I_{OH} = -2, -4, -8, -12, -18$		$V_{DD} - 0.4$	-	V_{DD}	V
Low-level output voltage	V_{OL}	$I_{OL} = 2, 4, 8, 12, 18$		V_{SS}	0	0.4	V
Input leakage current (Tri-state pin input) ⁴	I_{LI}	$V_I = 0V$ to V_{DD}		-10	-	10	μA
	I_{LZ}			-10	-	10	
Input pull-up/pull-down resistor ⁵	R_P	Pull-up $V_I = V_{DDI}$ Pull-down $V_I = 0V$		20	50	140	k Ω
Output Short-circuit current ⁶	I_O	Type	Condition	$V_O = V_{DD}$		$V_O = 0V$	mA
		Output buffer	Low power $I_{OL} = 2mA$	-20		+20	
			Normal $I_{OL} = 4mA$	-40		+40	
			Power $I_{OL} = 8mA$	-80		+80	
			High power $I_{OL} = 12mA$	-120		+120	
			Very high power $I_{OL} = 24mA$	-180		+180	

NOTES:

1. When $V_{IH} = V_{DD}$ and $V_{IL} = V_{SS}$, memory is in the standby mode.
2. If an input buffer with pull-up/pull-down resistor is used, the supply current may not be assured depending on the circuit configuration.
3. 5V interface is only for CMOS level.
4. If an input buffer with pull-up/pull-down resistor is used, the input leakage current may exceed the above value.
5. Either a buffer without a resistor or with a pull-up/pull-down resistor can be selected from the input and bidirectional buffers.
6. Maximum supply current at the short-circuit of output and V_{DD} or V_{SS} .

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Requirements		Unit
Supply voltage	V _{DDE}	(External) V _{SS} [*] −0.5 to 6.0		V
	V _{DDI}	(Internal) V _{SS} [*] −0.5 to 4.0		
Input voltage	V _I	V _{SS} [*] −0.5 to V _{DD} +0.5		V
Output voltage	V _O	V _{SS} [*] −0.5 to V _{DD} +0.5		V
Storage ambient temperature	T _{ST}	Plastic −55 to +125		°C
		Ceramic −65 to +150		
Supply pin current	I _D	For one V _{DD} pin	90	mA
		For one V _{SS} pin	90	
Output current	I _O	Low power-type output buffer I _{OL} = 2 mA	±14	mA
		Normal-type output buffer I _{OL} = 4mA	±14	
		Power-type output buffer I _{OL} = 8mA	±14	
		High-power type output buffer I _{OL} = 12mA	±21	
		Very high-power type of output buffer I _{OL} = 24mA	±58	

* $V_{SS} = 0\text{V}$

RECOMMENDED OPERATING CONDITIONS

Parameter		Symbol	Requirements			Unit
			Min.	Typ.	Max.	
Supply voltage		V_{DDE}	3.0	3.3	3.6	V
		V_{DDI}	3.0	3.3	4.6	
High-level input voltage	CMOS level	V_{IH}	$V_{DD} \times 0.7$	—	V_{DDI}	V
	TTL level		2.2	—	V_{DDI}	
Low-level input voltage	CMOS level	V_{IL}	V_{SS}^*	—	$V_{DDI} \times 0.2$	V
	TTL level		V_{SS}^*	—	0.8	
Junction temperature		T_j	0	—	100	$^{\circ}\text{C}$

* $V_{SS} = 0\text{V}$

THIRD PARTY EDA TOOL SUPPORTED

Fujitsu supports a third party environment allowing an ASIC designer the widest possible range of design options. Both the CG51 gate array and CE51 embedded array product families are fully supported by Fujitsu's ASIC design kits, running on leading workstations and provides a seamless link from leading third party ASIC design flows to Fujitsu's

ASIC back end environment. These kits provide an easy environment for design entry, design rule checking. They also provide a complete pre- and post-layout timing back annotating capabilities. The following leading third party tools are supported.

Cadence:	Verilog-XL
Mentor:	Design Architect 8.2, Autologic I, QuickSim II
Motive:	Motive 4.2 (Static Timing Analyzer)
Sunrise Systems:	ATPG 2.1
Synopsys:	Design Analyzer 3.2a, VSS

PACKAGE OPTIONS

In addition to offering plastic and ceramic versions of industry standard packages such as PQFPs and PGAs, Fujitsu also offers an impressive array of advanced packaging technology. Our long experience with high speed logic and thermal management has led us to develop some of the most advanced packaging available anywhere. From cost

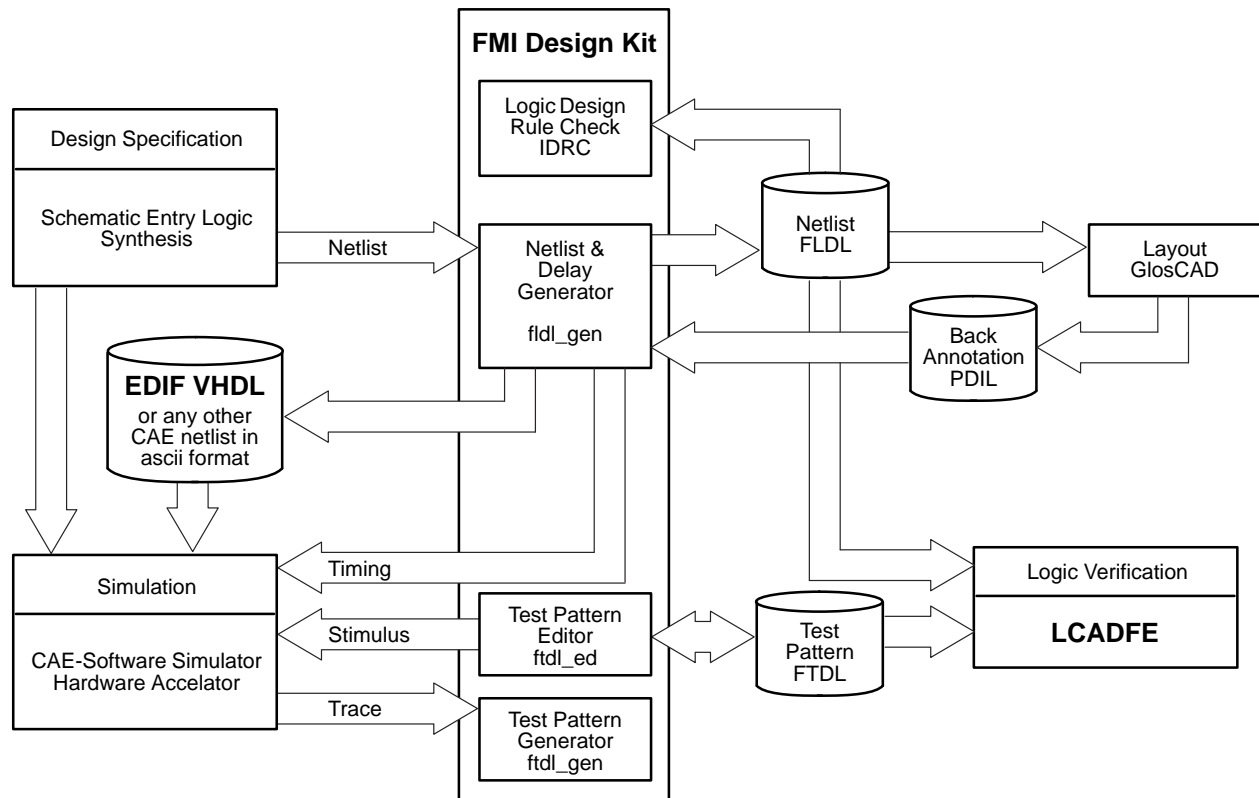
effective, single chip packages to sophisticated multichip modules, Fujitsu has a packaging option to suit your requirements. Whether you need a 208 PQFP, the newest in high I/O count surface mounted Ball Grid Array (BGA) packages or full custom packaging we can deliver the optimal solution.

Packaging Options

	343	114	164	214	284	364	484	654	754
Quad Flat Package (1.0, 0.8, 0.65 mm pin pitch)									
100	P								
120	P								C
160		P,C	P,C	P,C	P,C	P,C	P,C	P,C	
Shrink Quad Flat Package (0.5 mm pin pitch)									
80	P								
100	P								
120	P								
144		P	P	P	P				
176		P,C	P,C	P,C	P,C	P,C			
208		P,C	P,C	P,C	P,C	P,C	P,C	P,C	
240			P,C	P,C	P,C	P,C	P,C	P,C	
256				C	P,C	P,C	P,C	P,C	
304					C1	C1	C	C	C
Fine Pitch Flat Package (0.4 mm pin pitch)									
304						C	C	C	C
Pin Grid Array Package									
256					C	C	C	C	C
299					C	C	C	C	C
321						C	C	C	C
361							C	C	C
401						C	C	C	C
Ball Grid Array (BGA)									
256			P	P	P				
352					P	P	P		
416								P1	P1
576									P1

NOTES: 1 : Under Development
 C: Ceramic Package
 P: Plastic Package

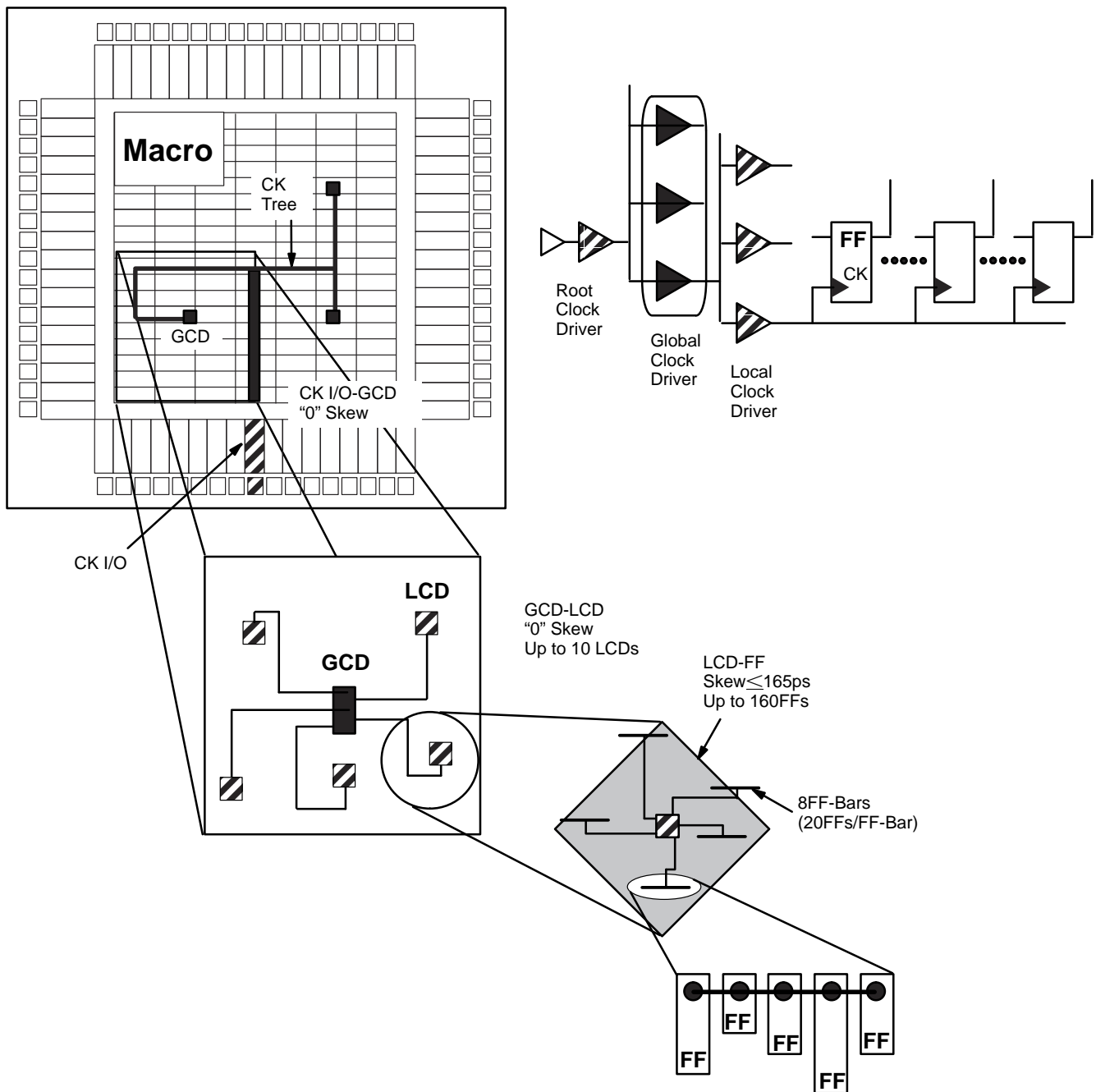
FRONT-END DESIGN FLOW



CLOCK SKEW CONTROL

To maximize performance in high speed, high density arrays, a designer must maintain tight clock skew control. In addition to an available PLL to manage interchip clock skew, Fujitsu's clock driven design methodology (CDDM) offers accurate on chip clock skew control. CDDM offers accurate RC extraction

of clock tree parameters, interactive clock tree implementation, simplifies trade-offs between clock tree delay and clock skew, early verification of potential design hold time errors and race conditions.



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This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields. However, it is advised that normal precautions be taken to avoid application of any voltage higher than maximum rated voltages to this high impedance circuit.

FUJITSU LIMITED

For further information please contact:

Japan

FUJITSU LIMITED
Electronic Devices International
Sales and Engineering Support Division
1015, Kamikodanaka Nakahara-ku,
Kawasaki 211, Japan
Tel: (044) 754-3753
FAX: (044) 754-3332

North and South America

FUJITSU MICROELECTRONICS, INC.
Logic Products Division
3545 North First Street
San Jose, CA 95134-1804, USA
Tel: 408-922-9000
FAX: 408-432-9044

Europe

FUJITSU MIKROELEKTRONIK GmbH
Am Siebenstein 6-10,
6072 Dreieich-Buchschlag,
Germany
Tel: (06103) 690-0
Telex: 411963
FAX: (06103) 690-122

Asia

FUJITSU MICROELECTRONICS ASIA PTE LIMITED
51 Bras Basah Road,
Plaza By The Park,
#06-04 to #06-07
Singapore 0719
Tel: 336-1600
Telex: 55573
FAX: 336-1609

Sales Offices

California

2880 Lakeside Drive, Suite 250
Santa Clara, CA 95054
(408) 982-1800

Century Center
2603 Main Street, #510
Irvine, CA 92714
(714) 724-8777

Colorado

12000 North Washington Street, #370
Thornton, CO 80241
(303) 254-9901

Georgia

3500 Parkway Lane, #210
Norcross, GA 30092
(404) 449-8539

Illinois

One Pierce Place, #1245
Itasca, IL 60143-2662
(708) 250-8580

Massachusetts

1000 Winter Street, #2500
Waltham, MA 02154
(617) 487-0029

Minnesota

3800 West 80th Street, #430
Bloomington, MN 55431-4419
(612) 893-5570

New York

898 Veterans Memorial Highway
Building 2, Suite 310
Hauppauge, NY 11788
(516) 582-8700

Oregon

15220 N.W. Greenbrier Parkway, #360
Beaverton, OR 97006
(503) 690-1909

Texas

14785 Preston Rd., #274
Dallas, TX 75240
(214) 233-9394

20515 SH 249, Suite 485
Houston, TX 77070
(713) 379-3030